

# Part Number: XRNI12W

# PHOTOTRANSISTOR

### **Features**

- Radial / Through hole package
- $\bullet$  Reliable & robust
- Low power consumption
- Available on tape and reel
- RoHS Compliant





# Package Schematics 8.6(0.339) 1.5(0.059)±1 Collector 0.7Max. □0.5(0.02)<sup>+0.25</sup> Recommended PCB Layout 0.9x2

### Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is  $\pm 0.25(0.01")$  unless otherwise noted.
- 3. Specifications are subject to change without notice.

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condiction
VBR CEO	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_{c}=100\mu A$ $E_{e}=0mW/cm^{2}$
VBR ECO	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_{\scriptscriptstyle E}$ = 100 $\mu$ A $E_{\rm e}$ = 0mW/cm $^2$
VCE(SAT)	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_{C}=2mA$ $E_{e}=20mW/cm^{2}$
Iceo	Collector Dark Current	-	-	100	nA	$V_{\mathrm{CE}} = 10 \mathrm{V}$ $E_{\mathrm{e}} = 0 \mathrm{mW/cm^2}$
$\mathrm{Tr}$	Rise Time (10% to 90%)	-	15	-	μs	$V_{\scriptscriptstyle \mathrm{CE}}$ = 5V $I_{\scriptscriptstyle \mathrm{C}}$ = 1mA $R_{\scriptscriptstyle L}$ = 1K $\Omega$
${ m TF}$	Fall Time (90% to 10%)	-	15	-	μs	
I(ON)	On State Collector Current	0.5	2.5	-	mA	$V_{\text{CE}} = 5V$ $E_{e} = 1 \text{mW/cm}^{2}$ $\lambda = 940 \text{nm}$
$\lambda_{0.1}$	Range of spectral bandwidth	420	-	1120	nm	-
$\lambda_{\mathrm{p}}$	Wavelength of peak sensitivity	-	940	-	nm	-
201/2	Angle of half sensitivity	-	20	-	deg	-

# Absolute Maximum Ratings at TA=25°C

 $\mathrm{Dec}\ 22{,}2018$ 

Parameter	Maximum Ratings		
Collector-to-Emitter Voltage	30V		
Emitter-to-Collector Voltage	5V		
Power Dissipation at (or below) 25°C Free Air Temperature	100mW		
Operating / Storage Temperature Range	-40 ∼ +85°C		
Lead Solder Temperature (>5mm for 5sec)	260°C		

A Relative Humidity between 40% and 60% is recommended in ESD-protected work areas to reduce static build up during assembly process (Reference JEDEC/JESD625-A and JEDEC/J-STD-033)

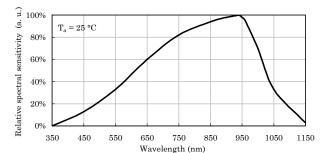
XDSA8078 V7 Layout: Maggie L.



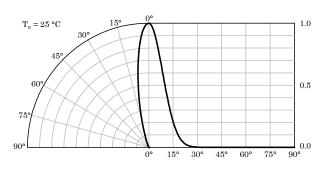
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### PHOTOTRANSISTOR

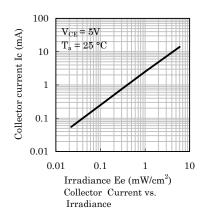


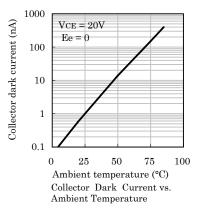


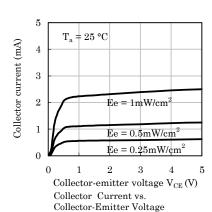
Relative Intensity Vs. CIE Wavelength

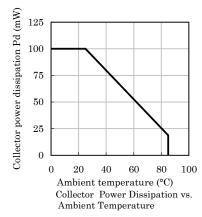


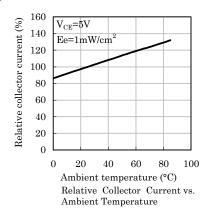
Spatial Distribution

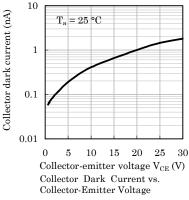




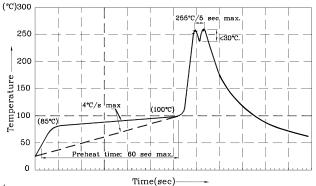








Wave Soldering Profile For Thru-Hole Products (Pb-Free Components)



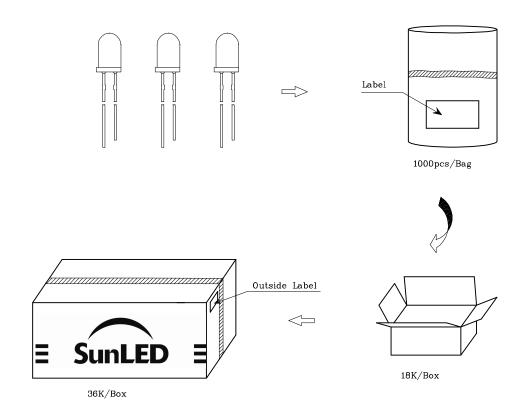
- Roles.

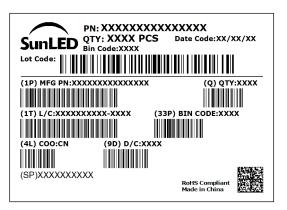
  1. Recommend pre-heat temperature of 105°C or less (as measured with a thermocouple attached to the LED pins) prior to immersion in the solder wave with a maximum solder bath temperature of 260°C.
- 2.Peak wave soldering temperature between 245°C  $\sim$  255°C for 3 sec (5 sec max).
- 3.Do not apply stress to the epoxy resin while the temperature is above 85°C. 4.Fixtures should not incur stress on the component when mounting and during soldering process.
  5.SAC 305 solder alloy is recommended.
  6.No more than one wave soldering pass.



PHOTOTRANSISTOR

# PACKING & LABEL SPECIFICATIONS





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